

In the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application.

1. (Currently Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer ~~including comprising~~ at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc,

said second electrode layer ~~comprising including at least one selected from a second metal group consisting of Ni, Pd and Co~~, and

said third electrode layer including Au.

2. (Original) The electrode structure according to claim 1, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

3. (Original) The electrode structure according to claim 1, wherein said second electrode layer has a thickness of 5 nm or more.

4. (Cancelled)

5. (Currently Amended) The electrode structure according to claim 1, wherein said first electrode layer ~~includes comprising~~ comprises a nitride of a metal included in said first metal group, and also ~~includes~~ comprises a compound of Ga and Co ~~a metal included in said second metal group~~.

6. (Cancelled)

7. (Cancelled)

8. (Currently Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

 said first electrode layer including comprising at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

 said second electrode layer comprising Ni, and

 said third electrode layer including comprising Au.

9. (Original) The electrode structure according to claim 8, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

10. (Original) The electrode structure according to claim 8, wherein said second electrode layer has a thickness of 5 nm or more.

11. (Cancelled)

12. (Currently Amended) The electrode structure according to claim 8, wherein said first electrode layer includes comprises a nitride of a metal included in said first metal group, and also includes comprises a compound of Ga and Ni a metal included in said second metal group.

13 – 18 (Cancelled)

19. (New) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

 said first electrode layer comprising at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc,

 said second electrode layer comprising Ni, and

 said third electrode layer comprising Au.

20. (New) The electrode structure according to claim 19, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

21. (New) The electrode structure according to claim 19, wherein said second electrode layer has a thickness of 5 nm or more.

22. (New) The electrode structure according to claim 19, wherein said first electrode layer comprises a nitride of a metal included in said first metal group, and also comprises a compound of Ga and Ni. ~~a metal included in said second metal group.~~

23. (New) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

 said first electrode layer comprising ~~at least one selected from a first metal group consisting of~~ Hf, and said second electrode layer comprising at least one selected from a second metal group consisting of Ni, Pd and Co, and

 said third electrode layer comprising including Au.

24. (New) The electrode structure according to claim 23, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

25. (New) The electrode structure according to claim 23, wherein said second electrode layer has a thickness of 5 nm or more.

26. (New) The electrode structure according to claim 23, wherein said first electrode layer comprises a nitride of a metal included in said first metal group, and also comprises includes a compound of Ga and a metal included in said second metal group.

27. (New) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively staked on said semiconductor layer;

 said first electrode layer comprising a mixture containing a nitride of at least one selected from a first metal group consisting of Hf, Zr, Nb, Ta and Sc, and a Ga compound comprising of at least one selected from a second metal group consisting of Ni or and Co,

 said second electrode layer comprising Ni, and

 said third electrode layer comprising Au.

28. (New) The electrode structure according to claim 27, wherein said second electrode layer has a thickness of 5 nm or more.

29. (New) The electrode structure according to claim 27, wherein said third electrode layer has a thickness of 5 nm or more.